

**13**

**14.** The method of claim **12** wherein the substrate layer includes a material selected from the group consisting of silicon, silicon-germanium, silicon-carbide, nickel, and gold.

**15.** The method of claim **12**, further comprising etching one or more portions of substrate layer and the second insulating layer.

**16.** The method claim **1**, wherein one or more of the first and second conductive layers include a material selected

**14**

from the group consisting of silicon, silicon-germanium, silicon-carbide, nickel, and gold.

**17.** The method of claim **1**, wherein the insulating layer includes a material selected from the group consisting of silicon oxide, silicon nitride, silicon carbide, high resistivity silicon, high resistivity silicon germanium, quartz, polyamide, and a polymeric film.

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